### **DISCRETE SEMICONDUCTORS**

# DATA SHEET

## BTA216 series D, E and F Three quadrant triacs guaranteed commutation

**Product specification** 

September 2018



### Three quadrant triacs guaranteed commutation

### BTA216 series D, E and F

### **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

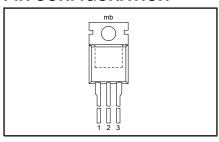
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
	BTA216- BTA216- BTA216-	600D 600E 600F	
$V_{DRM}$	Repetitive peak off-state	600	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	voltages RMS on-state current Non-repetitive peak on-state	16 140	A A

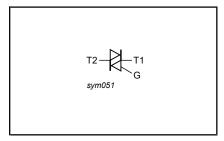
### **PINNING - TO220AB**

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

### PIN CONFIGURATION



### **SYMBOL**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	600¹	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 99 °C	-	16	Α
I <sub>TSM</sub>	Non-repetitive peak on-state current	full sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge			
12.	12.	t = 20 ms t = 16.7 ms	- -	140 150	A A A <sup>2</sup> s
l²t dl <sub>⊤</sub> /dt	l <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	$I_{TM} = 10 \text{ ms}$ $I_{TM} = 20 \text{ A}; I_{G} = 0.2 \text{ A};$ $I_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-	98 100	A <sup>2</sup> s A/μs
I <sub>GM</sub> P <sub>GM</sub>	triggering Peak gate current Peak gate power	00	- -	2 5	A W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$ $T_{j}$	Storage temperature Operating junction temperature		-40 -	150 125	Ç

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th } j\text{-mb}}$ $R_{\text{th } j\text{-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air		- - 60	1.2 1.7 -	K/W K/W K/W

### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA216-		D	E	F	
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$		_			
		T2+ G+ T2+ G-	-	5 5	10 10	25 25	mA mA
		T2- G-	-	5 5	10	25	mA
I <u>L</u>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ T2+ G+	_	15	25	30	mA
		T2+ G-	-	25	30	40	mA
		T2- G-	-	25	30	40	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	25	30	mA
					D, E, F		
V <sub>T</sub>	On-state voltage	$I_{T} = 20 \text{ A}$	-		1.5		V
V <sub>GT</sub>	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A} $ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25		1.5 -		V V
		$T_{i} = 125  ^{\circ}C$			0.5		
I <sub>D</sub>	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125  ^{\circ}C$	-		0.5		mA

### **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		MAX.	UNIT
		BTA216-	D	E	F		
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> = 67% V <sub>DRM(max)</sub> ; T <sub>j</sub> = 110 °C; exponential waveform; gate open circuit	30	60	70	-	V/μs
dl <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{V}/\mu\text{s}; \text{ gate}$	2.5	6.2	18	-	A/ms
dl <sub>com</sub> /dt	Critical rate of change of commutating current	open circuit $V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 0.1 \text{V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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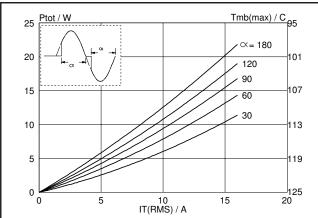


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha$  = conduction angle.

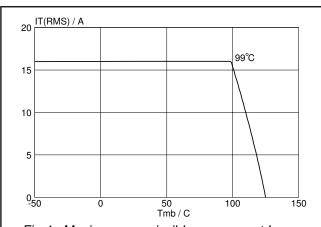


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

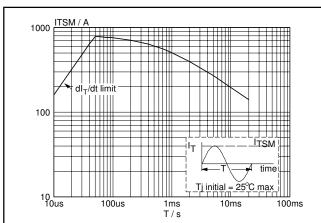


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

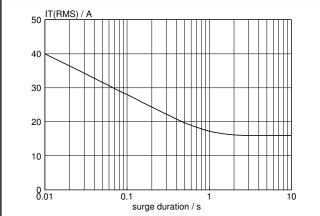


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 99$ °C.

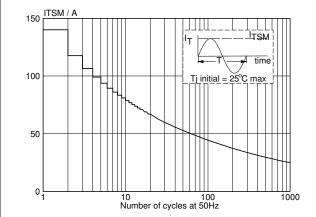


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

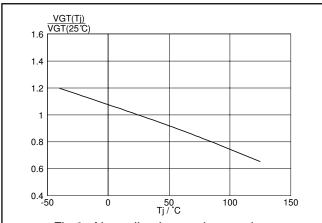
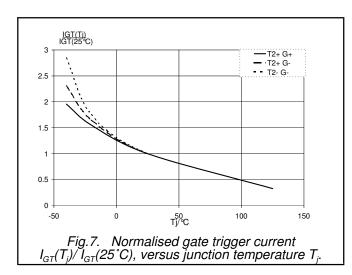


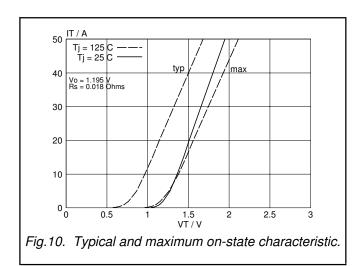
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_{j}$ .

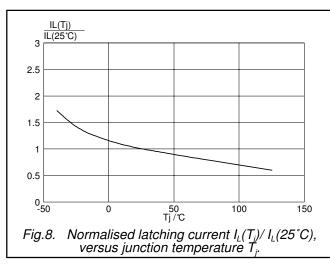
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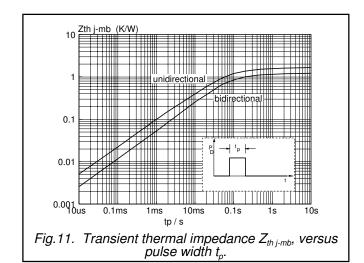
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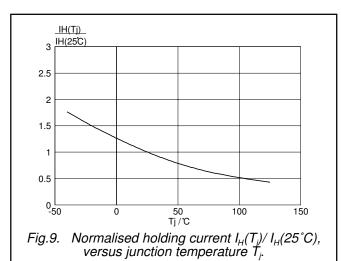
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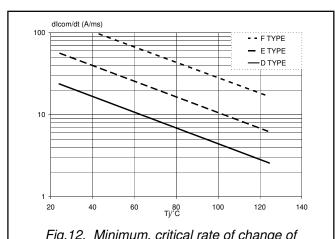


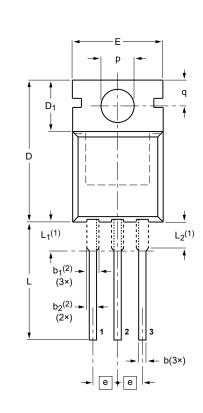
Fig.12. Minimum, critical rate of change of commutating current  $dl_{com}/dt$  versus junction temperature,  $dV_{com}/dt = 10V/\mu s$ .

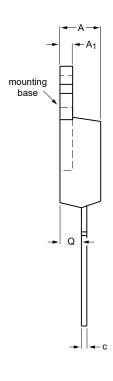
## Three quadrant triacs guaranteed commutation

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### **MECHANICAL DATA**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78





0 5 10 mm

### **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Lead shoulder designs may vary.
   Dimension includes excess dambar.

OUTLINE		REFERENCES EUROPEAI				ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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